

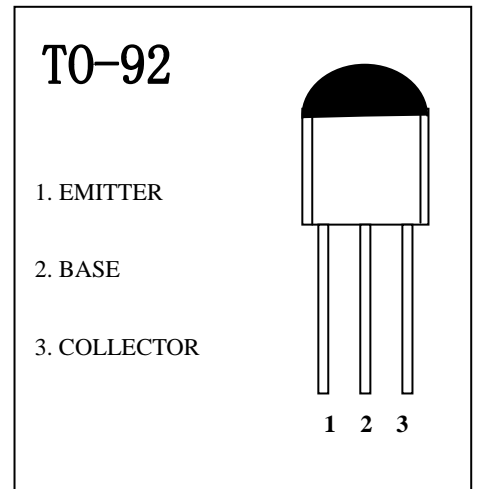
S8550 TRANSISTOR(PNP)

FEATURES

- Complimentary to S8050
- Collector Current: $I_c=0.5A$

MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	40	V
VCEO	Collector-Emitter Voltage	25	V
VEBO	Emitter-Base Voltage	5	V
IC	Collector Current-Continuous	0.5	A
PC	Collector Power Dissipation	0.3	W
TJ	Junction Temperature	150	°C
Tatg	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	$I_c=1mA, I_E=0$	40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	$I_c=1mA, I_B=0$	25			V
Emitter-base breakdown voltage	V(BR) _{EBO}	$I_c=1mA, I_c=0$	5			V
Collector cut-off current	ICBO	$V_{CB}=40V, I_E=0$			0.5	μA
Collector cut-off current	ICEO	$V_{ce}=25V, I_B=0$			1.0	μA
Emitter cut-off current	IEBO	$V_{EB}=5V, I_c=0$			0.1	μA
DC current gain	HFE	$V_{ce}=5V, I_c=1mA$	85		400	
Collector-emitter saturation voltage	VCE(sat)	$I_c=500mA, I_B=50mA$			0.6	V
Base-emitter saturation voltage	VBE(sat)	$I_c=500mA, I_B=50mA$			1.2	V
Gain Bandwidth Product	fT	$V_{CE}=6V, I_c=20mA, f=30MHz$	150			MHz